

多バンド超伝導体における パウリ常磁性効果

理研

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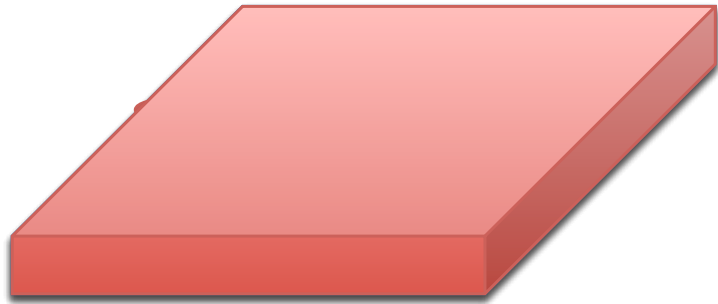
堤 康雅

市岡優典, 町田一成

謝辞：東大物性研

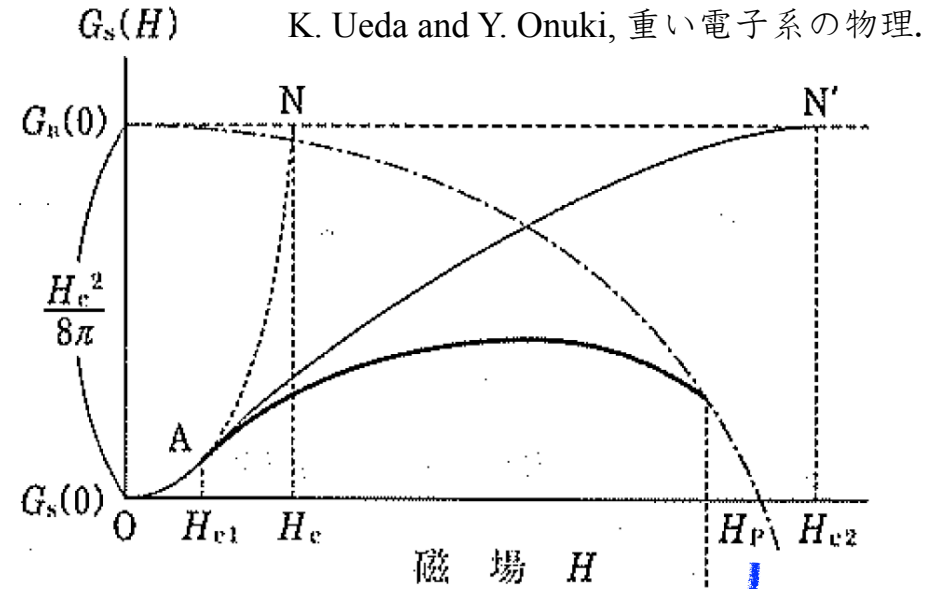
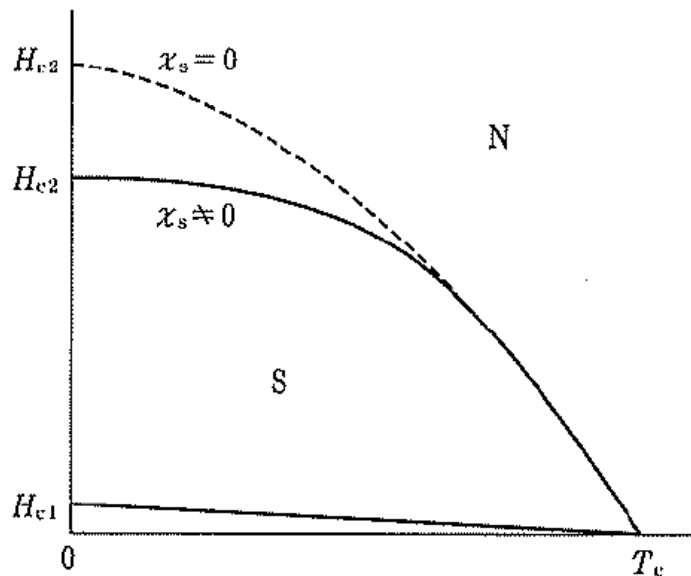
橘高俊一郎, 榊原俊郎

Pauli paramagnetic effect



渦系半径: ξ

$$H_{\text{orb}} = \frac{\phi_0}{2\pi\xi^2}$$



スピン帯磁率: $\chi_s \neq 0$

$$G_n(H) = G_n(0) - \frac{1}{2}\chi_s H^2$$

パウリリミット: $H_P = \frac{\Delta}{\sqrt{2}\mu_B}$

$$H_{c2} < H_P$$

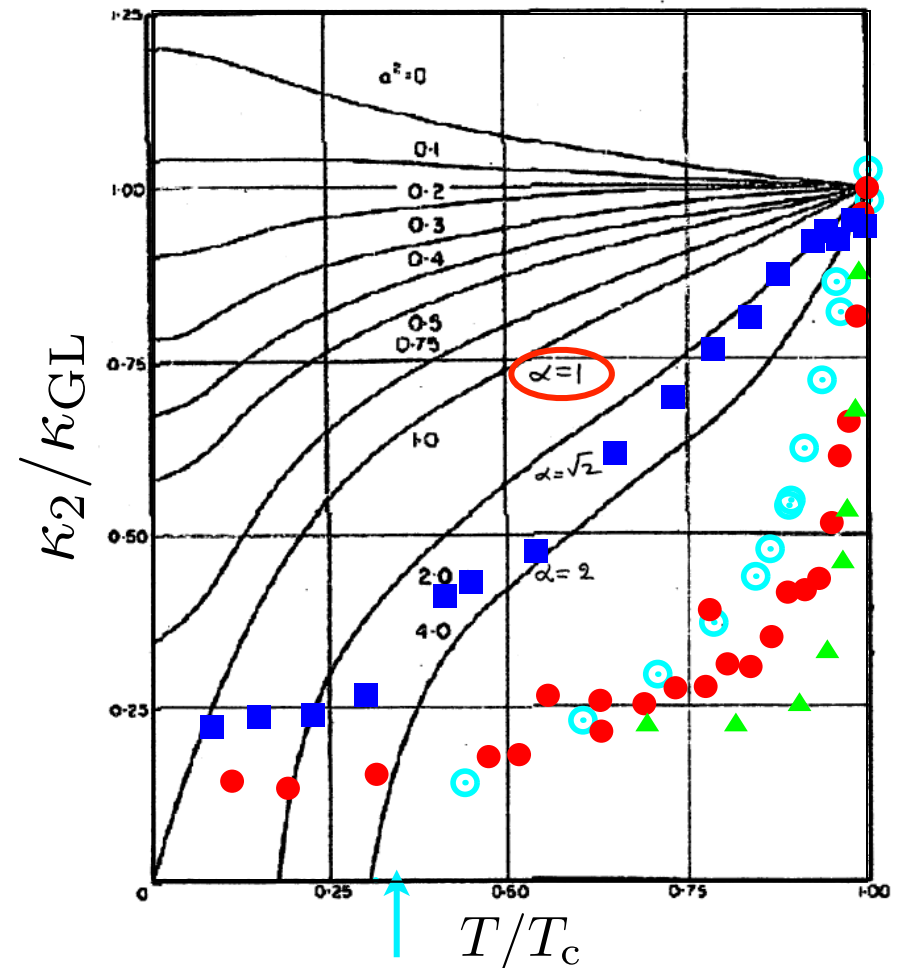
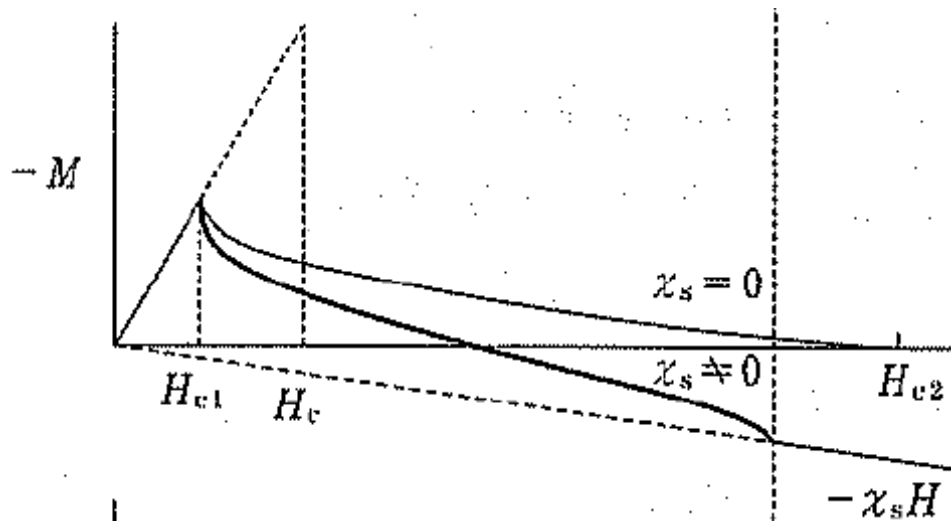
without FFLO

Maki parameter

$$\alpha \equiv \frac{\sqrt{2}H_{\text{orb}}}{H_P}$$

$$\left. \frac{d(M_s - M_n)}{dH} \right|_{H=H_{c2}} = \frac{1}{4\pi} \frac{1}{(2\kappa_2^2 - 1)\beta_A}$$

($\beta_A \approx 1.16$)
正三角渦格子



一次相転移

D. Saint-James *et al.*, *Type II Superconductivity* (1969).

○ CeCoIn₅: S. Ikeda *et al.*, *JPSJ* **70**, 2248 (2001).

● CeCu₂Si₂: S. Kittaka *et al.*, arXiv:1307.3499.

▲ UBe₁₃: Y. Shimizu *et al.*, *JPSJ* **80**, 093701 (2011).

■ KFe₂As₂: F. Hardy, private communication.

Two-band model

$$\Delta_1 > \Delta_2$$

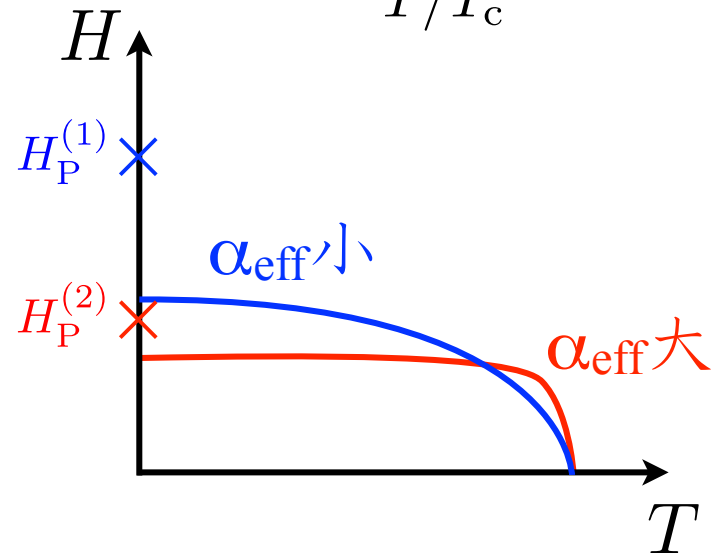
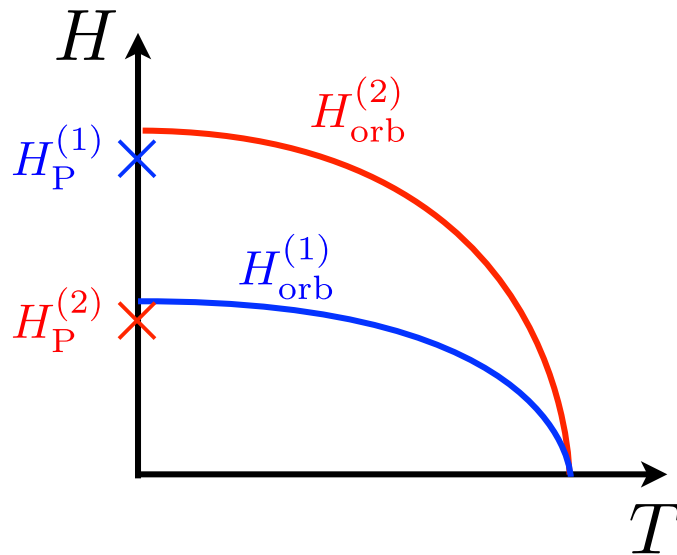
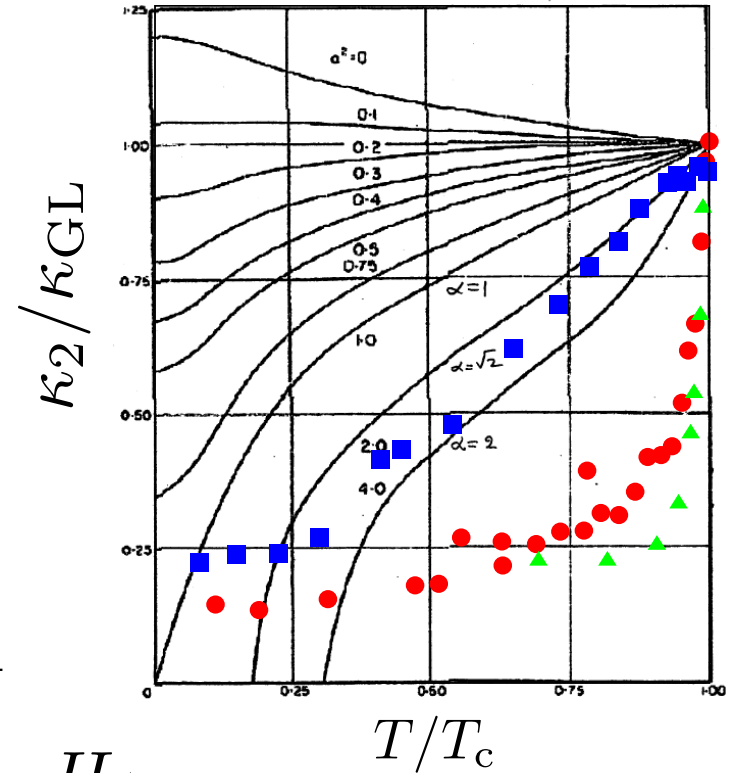
$$H_{\text{orb}}^{(1)} < H_{\text{orb}}^{(2)}$$

$$H_P = \frac{\Delta}{\sqrt{2}\mu_B} \text{ より、}$$

$$H_P^{(1)} > H_P^{(2)}$$

$$\alpha \equiv \frac{\sqrt{2}H_{\text{orb}}}{H_P}$$

$$\alpha_{\text{eff}}^{(1,2)} \equiv \frac{\sqrt{2}H_{\text{orb}}^{(1,2)}}{H_P^{(1,2)}}$$



Quasiclassical theory

Eilenberger equation

$$\begin{aligned}
 & -i\hbar \underline{v}_i \cdot \nabla \hat{g}(\mathbf{k}_i, \mathbf{r}, \omega_n + i\mu_B B) \\
 = & \left[\begin{pmatrix} i\omega_n - \underline{\mu}_B B + \underline{v}_i \cdot \mathbf{A}(\mathbf{r}) & -\underline{\Delta}_i(\mathbf{r}) \\ -\underline{\Delta}_i^*(\mathbf{r}) & -(i\omega_n - \underline{\mu}_B B + \underline{v}_i \cdot \mathbf{A}(\mathbf{r})) \end{pmatrix}, \hat{g}(\mathbf{k}_i, \mathbf{r}, \omega_n + i\mu_B B) \right]
 \end{aligned}$$

$$\hat{g} = -i\pi \begin{pmatrix} g & if \\ -if & -g \end{pmatrix} \quad \downarrow \quad \uparrow \quad \Delta_i, \mathbf{A}$$

Self-consistent condition

オーダー
パラメーター

$$\Delta_i(\mathbf{r}) = \sum_j N_{0j} \pi k_B T \sum_{|\omega_n| \leq \omega_c} \langle \underline{V}_{ij} f(\mathbf{k}_j, \mathbf{r}, \omega_n) \rangle_{\mathbf{k}_j}$$

ベクトル
ポテンシャル

超伝導電流

$$\mathbf{j}_s = - \sum_i N_{0i} \frac{T}{\kappa^2} \sum_{|\omega_n| \leq \omega_c} \langle \mathbf{v}_i \text{Im}\{g\} \rangle_{\mathbf{k}_i}$$

$$\mathbf{A} = \mathbf{B} \times \mathbf{r} / 2 + \mathbf{a} \quad \text{常磁性磁化}$$

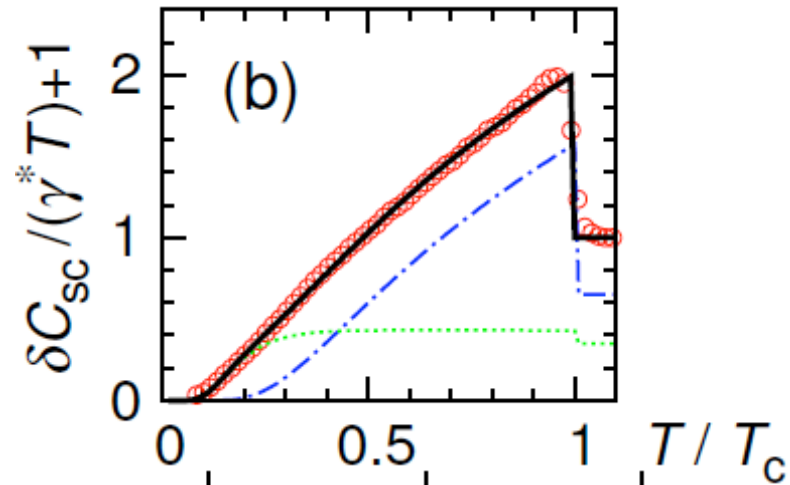
$$\nabla \times \nabla \times \mathbf{a} = \mathbf{j}_s + \nabla \times \underline{M}_{\text{para}} \quad M_{\text{para}} = \frac{B(\mathbf{r})}{B} - \sum_i N_{0i} \frac{T}{\mu_B B} \sum_{|\omega_n| \leq \omega_c} \langle \text{Im}\{g\} \rangle_{\mathbf{k}_i}$$

Density of states (DOS)

$$N_{i\sigma}(E) = \frac{1}{S} \int dS N_{i\sigma}(\mathbf{r}, E) = \frac{1}{S} \int dS \underline{N}_{0i} \langle \text{Re}[g(\mathbf{k}_i, \mathbf{r}, \omega_n + i\sigma\mu_B B)]_{i\omega_n \rightarrow E+i\eta} \rangle_{\mathbf{k}_i}$$

LDOS

Parameter



CeCu₂Si₂: S. Kittaka *et al.*, arXiv:1307.3499.

s-wave two-gap model

$$N_{01} : N_{02} = 65 : 35$$

$$\frac{\Delta_1}{k_B T_c} = 1.76, \quad \frac{\Delta_2}{k_B T_c} = 0.7$$

$$N_{01} : N_{02} = 2 : 1$$

$$\Delta_1 : \Delta_2 \sim 2 : 1$$

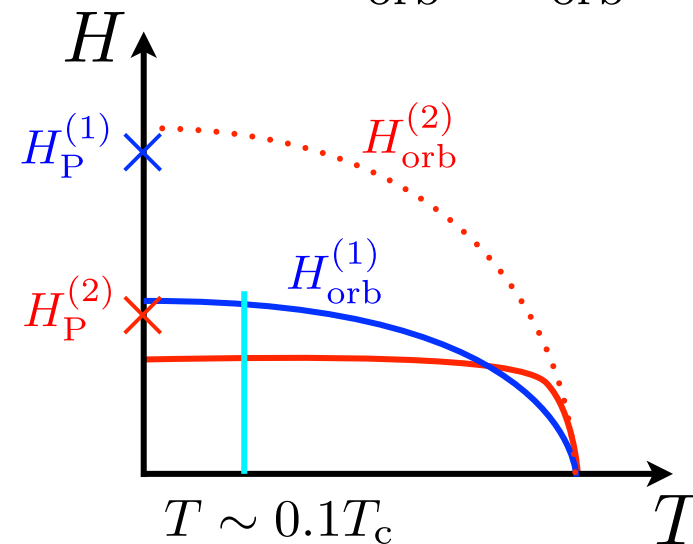
$$V_{11} = V_0, \quad V_{22} = 1.5V_0,$$

$$V_{12} = V_{21} = 0.05V_0$$

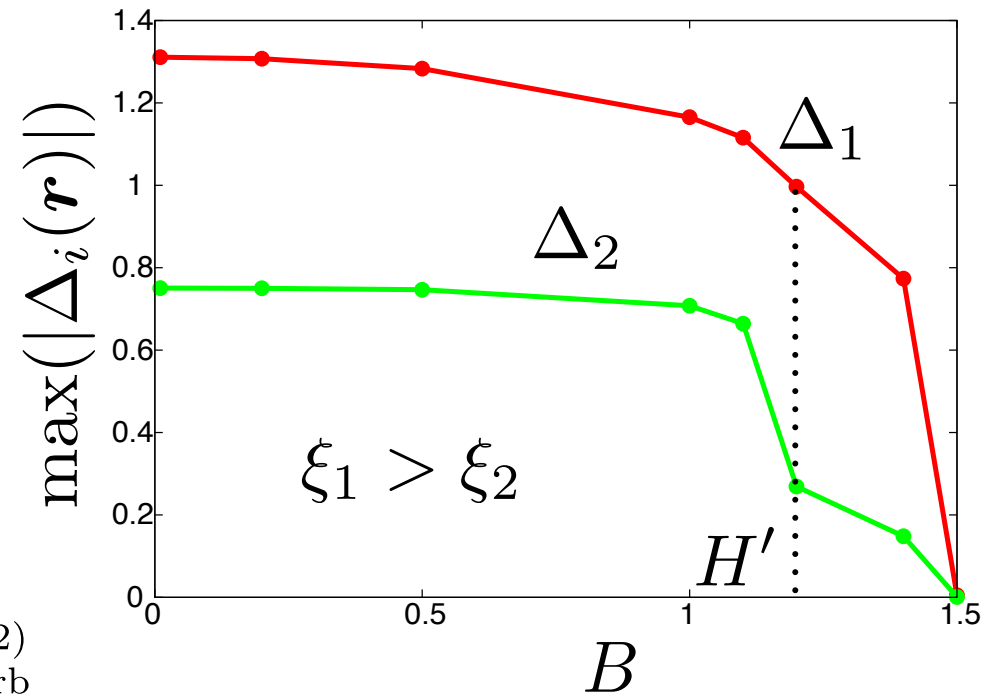
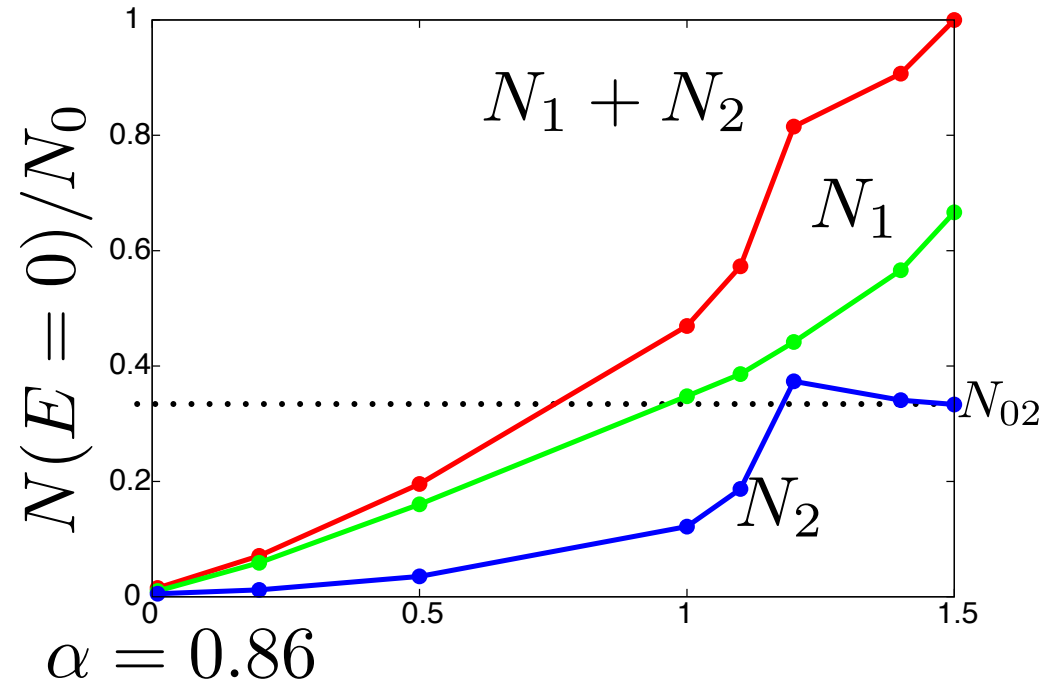
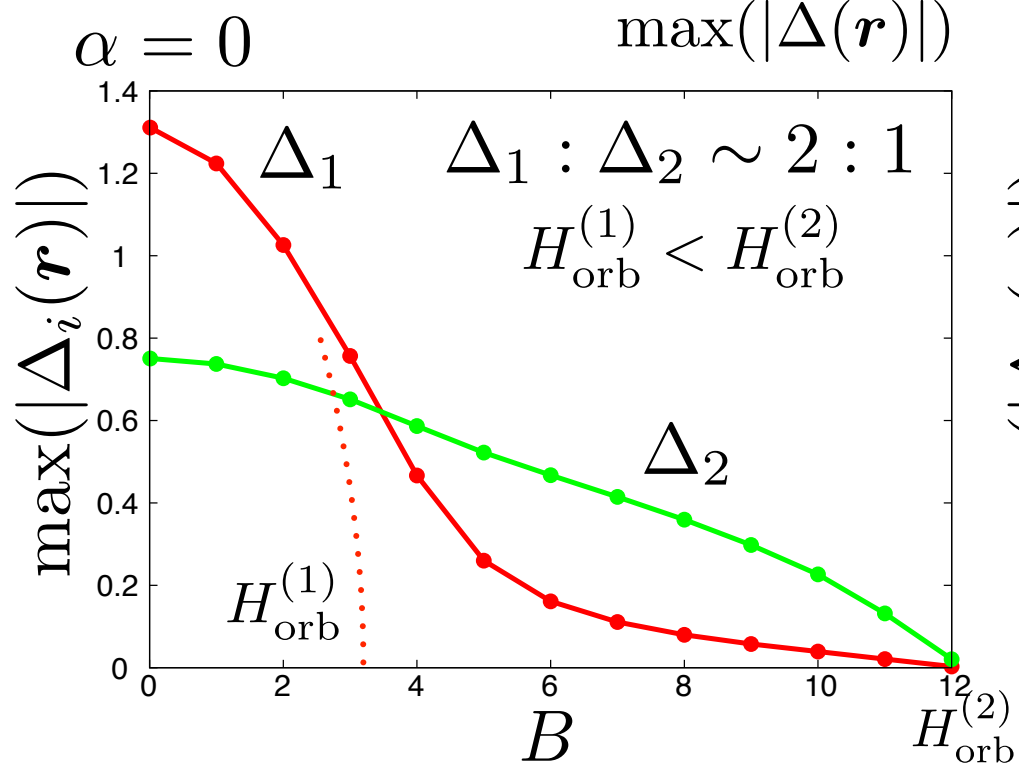
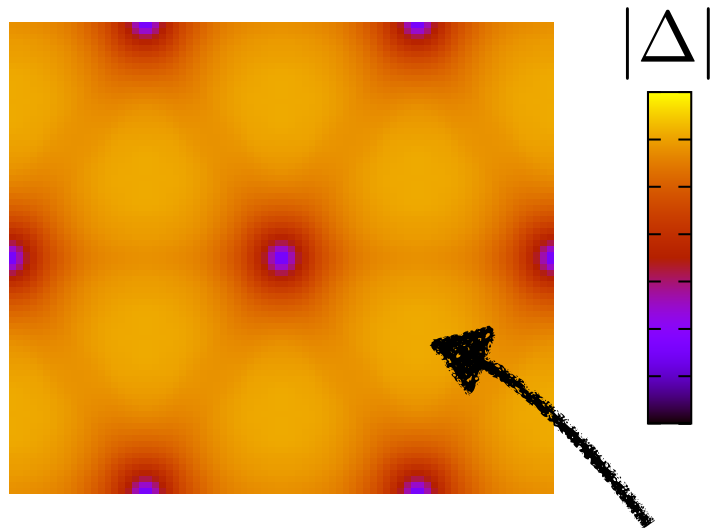
$$H_{\text{orb}} \sim \frac{\Phi_0}{2\pi\xi^2} \sim \frac{\Phi_0}{2\pi\hbar^2} \left(\frac{\Delta}{v_F} \right)^2 \text{ より、}$$

$$v_{F1} : v_{F2} = 4 : 1$$

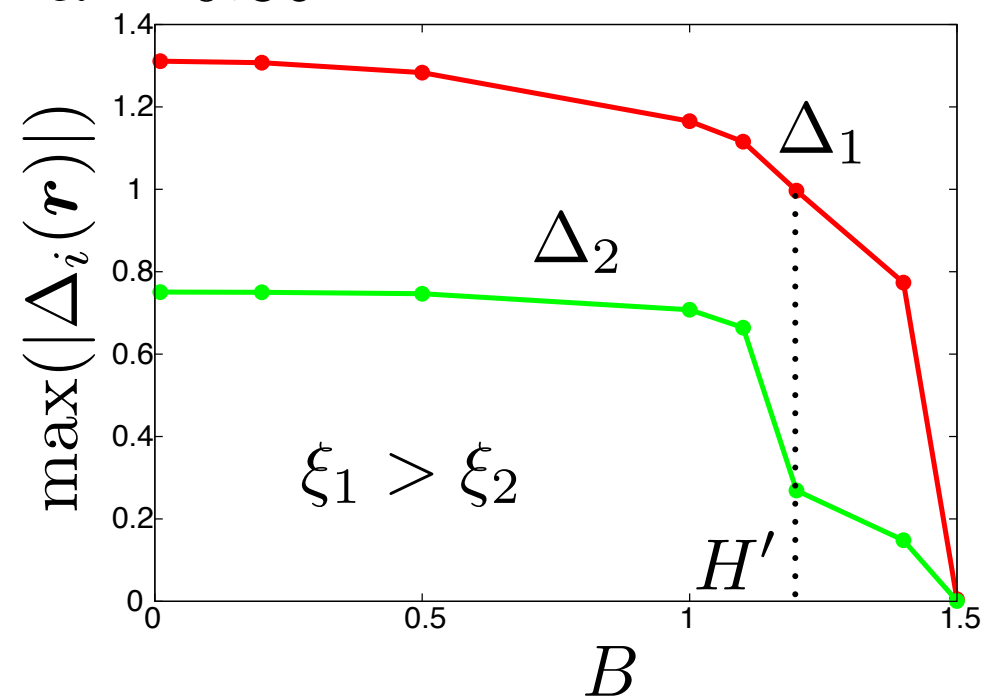
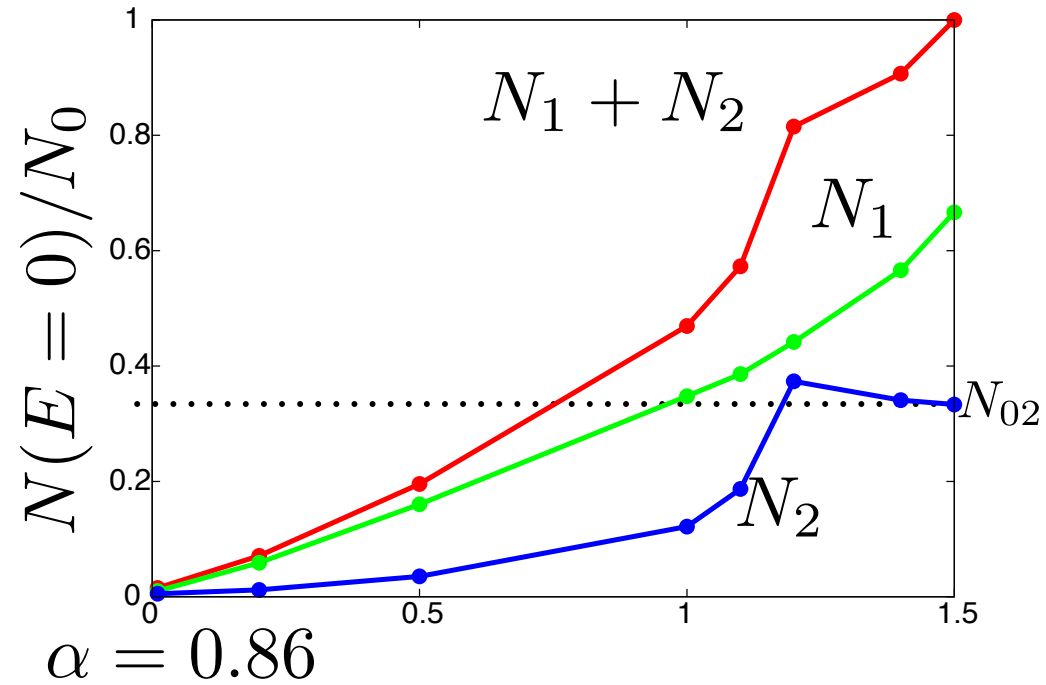
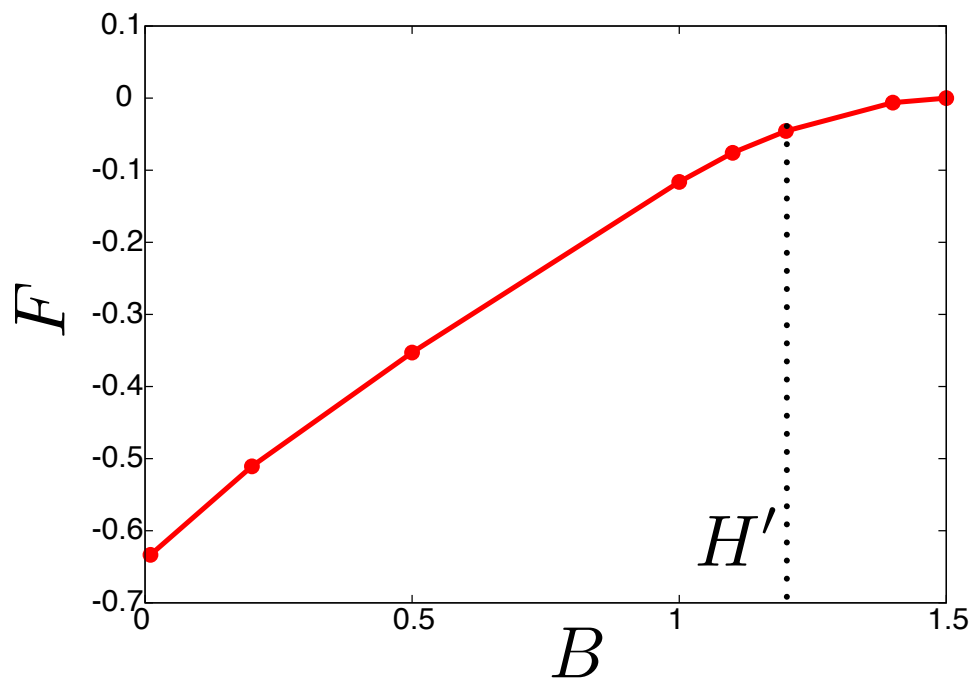
$$\Rightarrow H_{\text{orb}}^{(1)} : H_{\text{orb}}^{(2)} \sim 1 : 4$$



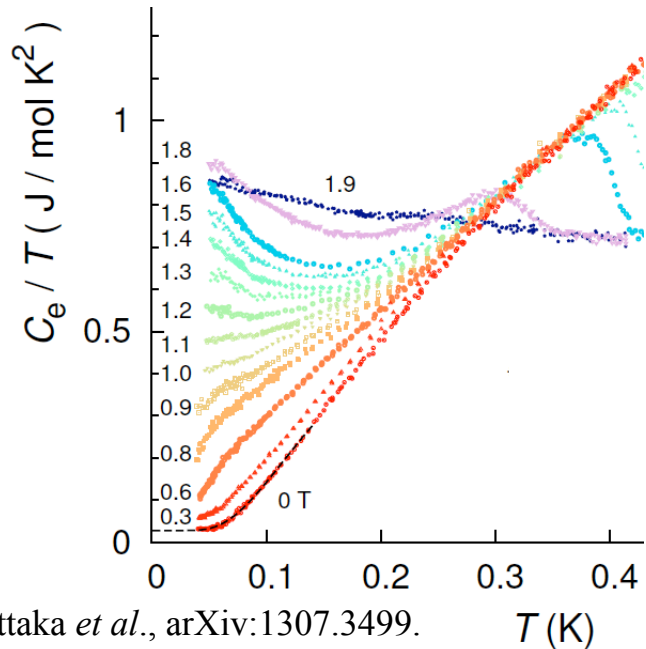
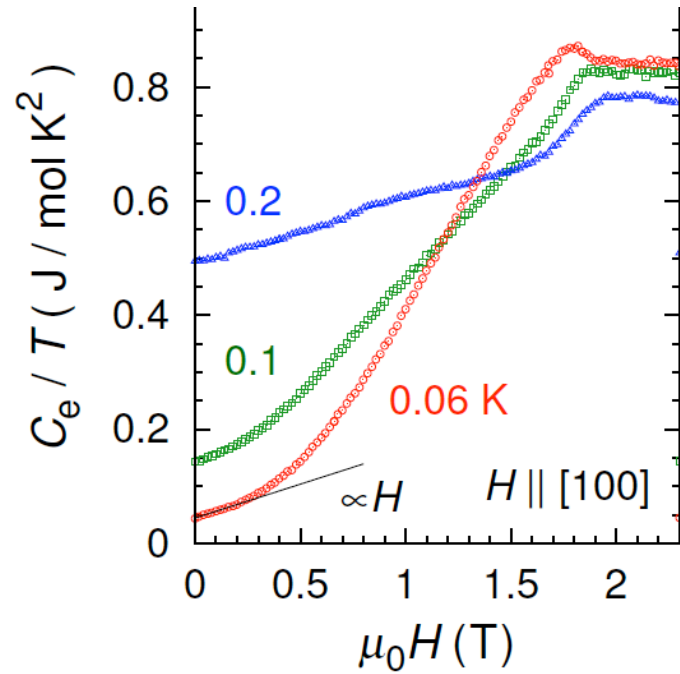
Field dependence



Field dependence



CeCu₂Si₂



$$C_e = T \frac{dS}{dT} = \int N(E) dE E \frac{\partial f(E)}{\partial T}$$

$$(E \rightarrow xT) = \int N(xT) T dx \frac{x^2}{4 \cosh^2(x/2)}$$

$$\frac{C_e}{T} \equiv \gamma(T) = \int N(xT) dx \frac{x^2}{4 \cosh^2(x/2)}$$

$T \rightarrow 0$ のとき,

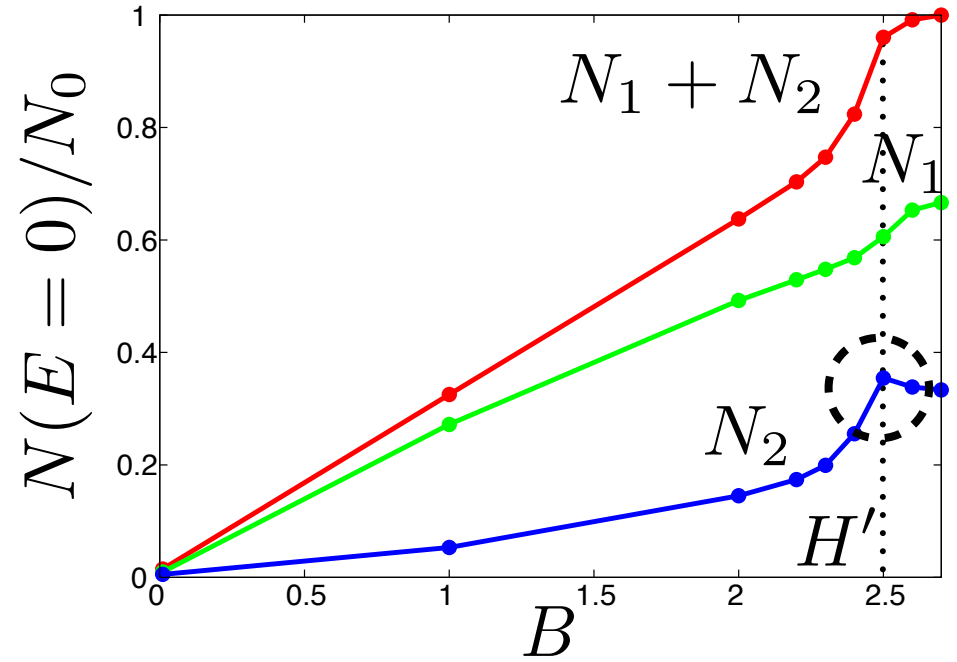
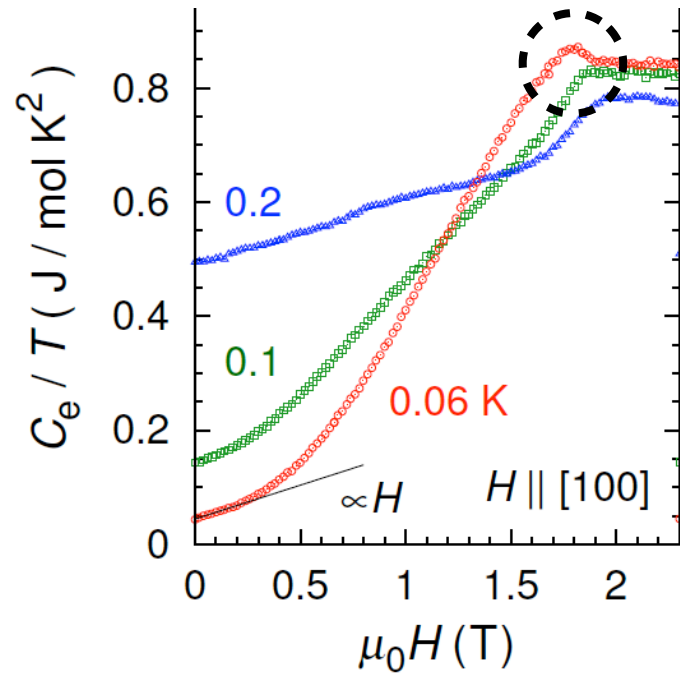
$$\gamma \propto N(0)$$

$N(E) = a|E|^n$ のとき,

$$\frac{C_e}{T} = \int aT^n dx \frac{|x|^{2+n}}{4 \cosh^2(x/2)} \propto T^n$$

CeCu₂Si₂

$$\alpha = 0.34$$

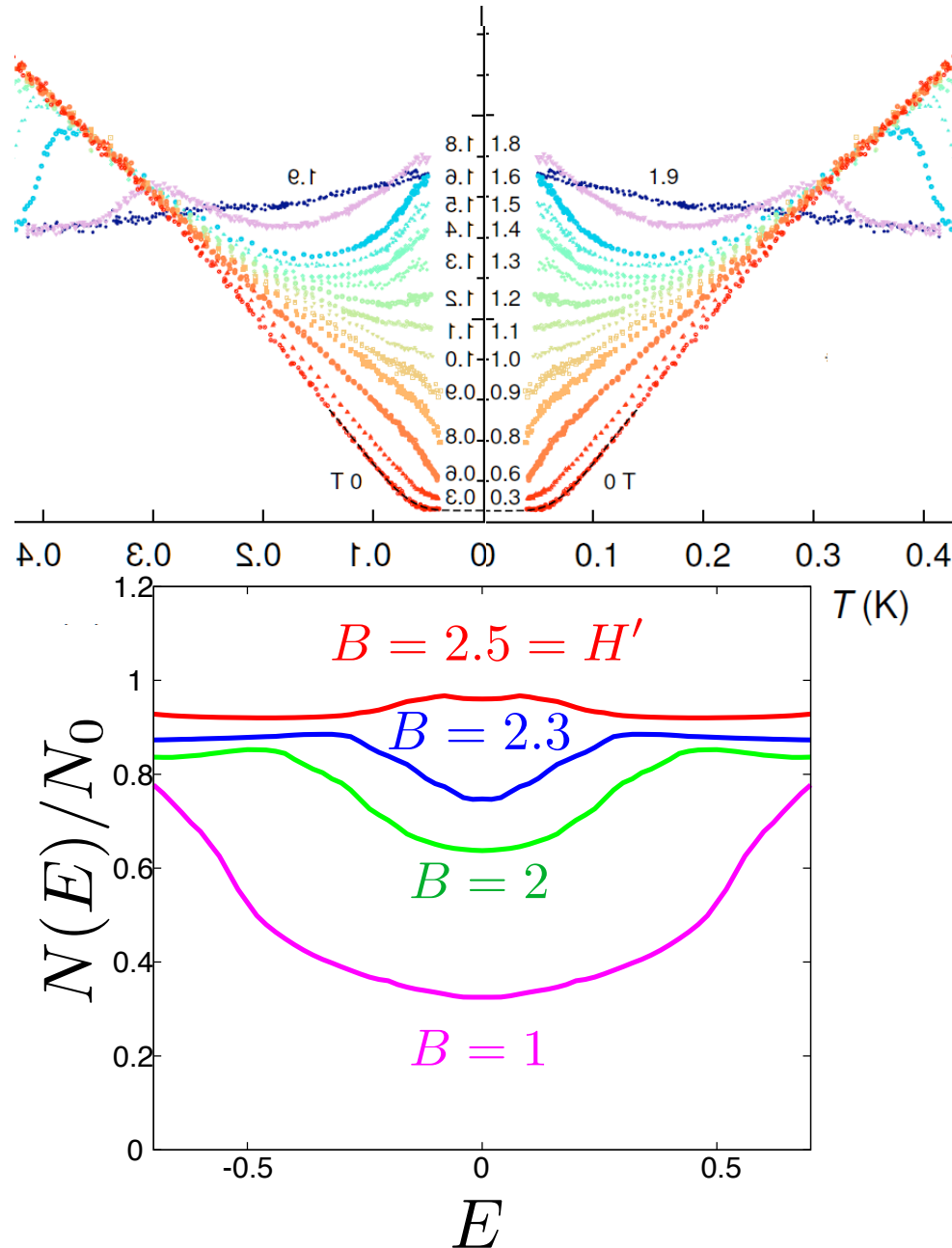


$T \rightarrow 0$ のとき,
 $\gamma \propto N(0)$

CeCu₂Si₂

$N(E) = a|E|^n$ のとき,

$$\frac{C_e}{T} \propto T^n$$



Summary

- 📌 パウリ常磁性効果の理論を多バンド超伝導体にも適用できるように拡張.
- 📌 一つのバンドのペア振幅が激減する H' が存在し、ゼロエネルギー状態密度がノーマル状態を越える.
- 📌 パウリ常磁性効果が強く効いていても一次相転移が起こらないことがあり得る.
- 📌 CeCu_2Si_2 の比熱の振る舞いは本理論により理解することができる.

